

BCP53-16

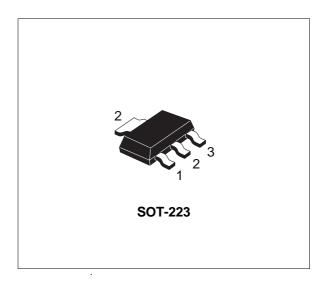
LOW POWER PNP TRANSISTOR

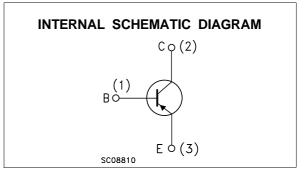
Ordering Code	Marking	
BCP53-16	BCP5316	

- SILICON EPITAXIAL PLANAR PNP MEDIUM VOLTAGE TRANSISTOR
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS BCP56-16

APPLICATIONS

- MEDIUM VOLTAGE LOAD SWITCH TRANSISTORS
- OUTPUT STAGE FOR AUDIO AMPLIFIERS CIRCUITS
- AUTOMOTIVE POST-VOLTAGE REGULATION





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
Vсво	Collector-Base Voltage $(I_E = 0)$	-100	V	
V_{CEO}	Collector-Emitter Voltage $(I_B = 0)$	-80	V	
VCER	Collector-Emitter Voltage ($R_{BE} = 1K\Omega$)	-100	V	
V _{EBO}	Emitter-Base Voltage (I _C = 0)	-5	V	
Ιc	Collector Current	-1	A	
Ісм	Collector Peak Current (t _p < 5 ms)	-1.5	A	
IB	Base Current	-0.1	A	
I _{BM}	Base Peak Current (t _p < ms)	-0.2	A	
Ptot	Total Dissipation at T _{amb} = 25 °C	1.6	W	
T _{stg}	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

September 2003

THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	78	°C/W
 Device moun 	ted on a PCB area of 1 cm ²			

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \, {}^{\circ}C$ unless otherwise specified)

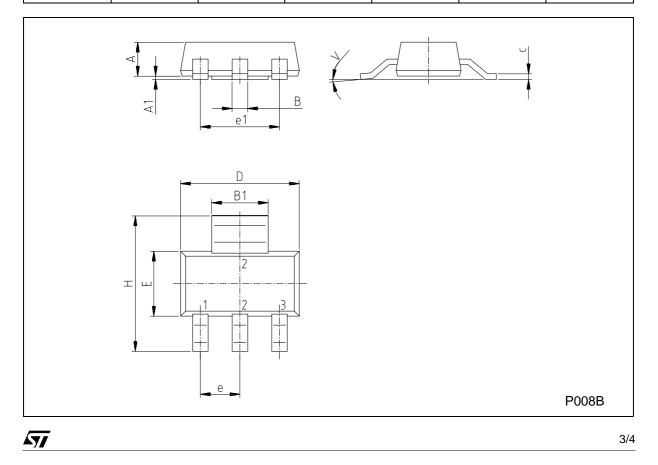
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I _E = 0)	$V_{CB} = -30 V$ $V_{CB} = -30 V$ $T_j = 125 \ ^{o}C$			-100 -10	nA μA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA	-100			V
$V_{(BR)CEO^*}$	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -20 mA	-80			V
V _{(BR)CER}	Collector-Emitter Breakdown Voltage ($R_{BE} = 1 K\Omega$)	I _C = -100 μA	-100			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA	-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{C} = -500 \text{ mA}$ $I_{B} = -50 \text{ mA}$			-0.5	V
$V_{BE(on)}*$	Base-Emitter On Voltage	$I_{C} = -500 \text{ mA}$ $V_{CE} = -2 \text{ V}$			-1	V
h _{FE} *	DC Current Gain		40 100 25		250	
f⊤	Transition Frequency	$I_{C} = -10 \text{ mA} \text{ V}_{CE} = -5 \text{ V} \text{ f} = 20 \text{ MHz}$		50		MHz

57

 \ast Pulsed: Pulse duration = 300 $\mu s,$ duty cycle \leq 1.5 %

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			1.80			0.071
В	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
С	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
е		2.30			0.090	
e1		4.60			0.181	
Е	3.30	3.50	3.70	0.130	0.138	0.146
Н	6.70	7.00	7.30	0.264	0.276	0.287
V			10 [°]			10 [°]

SOT-223 MECHANICAL DATA



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics. The ST logo is a trademark of STMicroelectronics.

The ST logo is a trademark of ST Microelectronics.

All other names are the property of their respective owners.

© 2003 STMicroelectronics – All Rights reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

57

4/4